

# NPN SILICON GERMANIUM RF TRANSISTOR NESG2046M33

### NPN SiGe RF TRANSISTOR FOR LOW NOISE, HIGH-GAIN AMPLIFICATION 3-PIN SUPER LEAD-LESS MINIMOLD (M33, 0804 PACKAGE)

#### FEATURES

- The device is an ideal choice for low noise, high-gain amplification  
NF = 0.8 dB TYP.,  $G_a = 11.5$  dB TYP. @  $V_{CE} = 1$  V,  $I_c = 3$  mA,  $f = 2$  GHz
- High breakdown voltage technology for SiGe Tr. adopted:  $V_{CE0}$  (absolute maximum ratings) = 5.0 V
- 3-pin super lead-less minimold (M33, 0804 package)

#### ORDERING INFORMATION

Part Number	Quantity	Supplying Form
NESG2046M33	50 pcs (Non reel)	<ul style="list-style-type: none"> <li>8 mm wide embossed taping</li> <li>Pin 2 (Base) face the perforation side of the tape</li> </ul>
NESG2046M33-T3	10 kpcs/reel	

**Remark** To order evaluation samples, contact your nearby sales office.  
Unit sample quantity is 50 pcs.

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = +25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	$V_{CBO}$	13	V
Collector to Emitter Voltage	$V_{CEO}$	5	V
Emitter to Base Voltage	$V_{EBO}$	1.5	V
Collector Current	$I_c$	40	mA
Total Power Dissipation	$P_{tot}$ <sup>Note</sup>	130	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-65 to +150	$^\circ\text{C}$

**Note** Mounted on  $1.08 \text{ cm}^2 \times 1.0 \text{ mm}$  (t) glass epoxy PCB

**Caution** Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = +25°C)**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> = 5 V, I <sub>E</sub> = 0 mA	–	–	100	nA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> = 0.5 V, I <sub>C</sub> = 0 mA	–	–	100	nA
DC Current Gain	h <sub>FE</sub> <sup>Note 1</sup>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 2 mA	140	180	220	–
RF Characteristics						
Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 15 mA, f = 2 GHz	15	18	–	GHz
Insertion Power Gain	S <sub>21e</sub>   <sup>2</sup>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 15 mA, f = 2 GHz	11	13	–	dB
Noise Figure	NF	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 3 mA, f = 2 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	–	0.8	1.5	dB
Associated Gain	G <sub>a</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 3 mA, f = 2 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	9.5	11.5	–	dB
Reverse Transfer Capacitance	C <sub>re</sub> <sup>Note 2</sup>	V <sub>CB</sub> = 1 V, I <sub>E</sub> = 0 mA, f = 1 MHz	–	0.2	0.4	pF

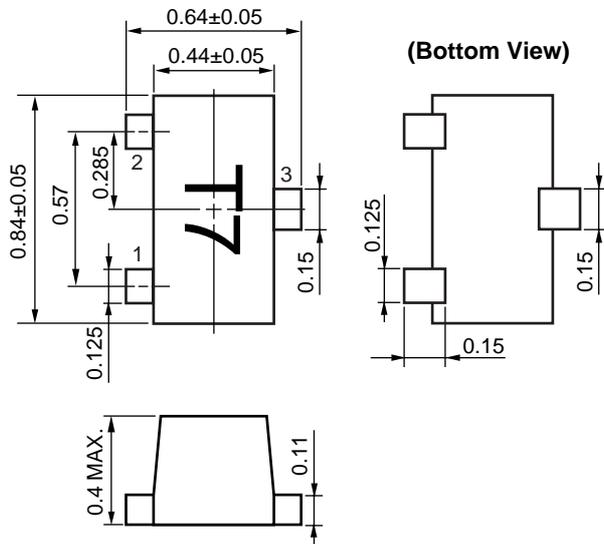
- Notes** 1. Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%  
 2. Collector to base capacitance when the emitter grounded

**h<sub>FE</sub> CLASSIFICATION**

Rank	FB
Marking	T7
h <sub>FE</sub> Value	140 to 220

PACKAGE DIMENSIONS

3-PIN SUPER LEAD-LESS MINIMOLD (M33, 0804 PACKAGE) (UNIT: mm)



PIN CONNECTIONS

1. Emitter
2. Base
3. Collector

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**NEC Compound Semiconductor Devices, Ltd.** <http://www.ncsd.necel.com/>

E-mail: [salesinfo@ml.ncsd.necel.com](mailto:salesinfo@ml.ncsd.necel.com) (sales and general)

[techinfo@ml.ncsd.necel.com](mailto:techinfo@ml.ncsd.necel.com) (technical)

5th Sales Group, Sales Division TEL: +81-44-435-1588 FAX: +81-44-435-1579

**NEC Compound Semiconductor Devices Hong Kong Limited**

E-mail: [ncsd-hk@elhk.nec.com.hk](mailto:ncsd-hk@elhk.nec.com.hk) (sales, technical and general)

Hong Kong Head Office TEL: +852-3107-7303 FAX: +852-3107-7309

Taipei Branch Office TEL: +886-2-8712-0478 FAX: +886-2-2545-3859

Korea Branch Office TEL: +82-2-558-2120 FAX: +82-2-558-5209

**NEC Electronics (Europe) GmbH** <http://www.ee.nec.de/>

TEL: +49-211-6503-01 FAX: +49-211-6503-487

**California Eastern Laboratories, Inc.** <http://www.cel.com/>

TEL: +1-408-988-3500 FAX: +1-408-988-0279